**IN THE SPECIFICATION:**

Please amend the specification, as follows:

Please amend the paragraph on page 24, from lines 3 to 19, as follows:

In the circuit of FIG. 3, the impedance at the point D is 50 Ω when a load connected to the output terminal OUT is 50 Ω and the impedance at the point A as the drain terminal of the FET 213 is converted to about 2 Ω by the matching circuit 244, as indicated by the arrow [[X]] on the Smith chart shown in FIG. 7. When the impedance of the load connected to the output terminal OUT changes along a circumference centering around the point of 50 Ω, as indicated by the sign Z1 in FIG. 7, the impedance at the point D naturally changes in the same manner along the circumference Z1. At this time, the impedance at the point A changes along the circumference Z2 centering around the impedance (2 Ω) at the point A when the load is 50 Ω. If a comparison is made between the points A and D, the point A is at a lower impedance so that it changes along the circumference Z2 with a smaller radius. Accordingly, the voltage variations in response to the load fluctuations are larger at the point D than at the point A.

Please amend the paragraph bridging pages 29 and 30, from line 19 on page 29 to line 15 on page 30, as follows:

In FIG. 10, ANT denotes an antenna for transmitting and receiving a signal wave and 100 denotes an electronic device (hereinafter referred to as an RF device) composed of a semiconductor integrated circuit for processing high frequency signals (baseband IC), bandpass filters BPF1 and BPF2 each for removing a harmonic component from a signal to be transmitted, bandpass filters BPF3 and BPF4 each for removing an unwanted wave from a received signal, and the like, which are mounted on a single package. The baseband IC comprises: a modulation/demodulation circuit capable of performing GMSK modulation/demodulation in GSM and DCS systems; a high frequency signal processing circuit (baseband circuit) 110 having a circuit for generating signals I and Q based on data to be transmitted (baseband signal) and processing the signals I and Q extracted from the received signal; and low noise amplifiers LNA1 [[LAN1]] and LNA2 [[LAN2]] for amplifying the received signal, which are formed on a single semiconductor chip. In the baseband circuit 110, Tx-MIX1 and Tx-MIX2 are respective mixers for up-converting GSM and DCS signals to be transmitted and Rx-MIX1 and Rx-MIX2 are respective mixers for

down-converting GSM and DCS received signals.

Please amend the paragraph bridging pages 31 and 32, from line 25 on page 31 to line 9 on page 32, as follows:

A mode selection signal Vmode representing either the GSM or DCS mode is supplied from the baseband circuit 110 to the bias circuit 230 such that the bias circuit 230 generates, based on the control signal Vmode, the bias current in accordance with the mode and supplies the generated bias current to either of the power amplifiers 210a and 210b. The bias circuit 230 may also be constructed to determine which one of the currents Icont1H and Icont1L is supplied from the RF device 110 and perform switching in the bias circuit 230 [[210]] based on the result of the determination.